

Supporting Information

Facile fabrication of ultrathin graphene papers for effective electromagnetic shielding

Wei-Li Song,^{†, §} Li-Zhen Fan,^{†,*} Mao-Sheng Cao,^{‡,*} Ming-Ming Lu,[‡] Chan-Yuan Wang,^{||} Jia Wang,[†] Tian-Tian Chen,[†] Yong Li,[‡] Zhi-Ling Hou,^{‡,§} Jia Liu,[‡] Ya-Ping Sun[§]

[†]*Institute of Advanced Materials and Technology, University of Science and Technology Beijing, Beijing, 100083, P. R. China.*

[‡]*School of Materials Science and Engineering, Beijing Institute of Technology, Beijing, 100081, P. R. China.*

[§]*Department of Chemistry and Laboratory for Emerging Materials and Technology, Clemson University, Clemson, South Carolina 29634-0973, USA.*

^{||}*310 Department, 3rd Institution of China Aerospace Science & Industry, Beijing 100071, P. R. China.*

* Corresponding Authors: Tel/Fax: +86 10 6233-3548, +86 10 6891-4062.

Email: fanlizhen@ustb.edu.cn (Li-Zhen Fan), caomaosheng@bit.edu.cn (Mao-Sheng Cao).

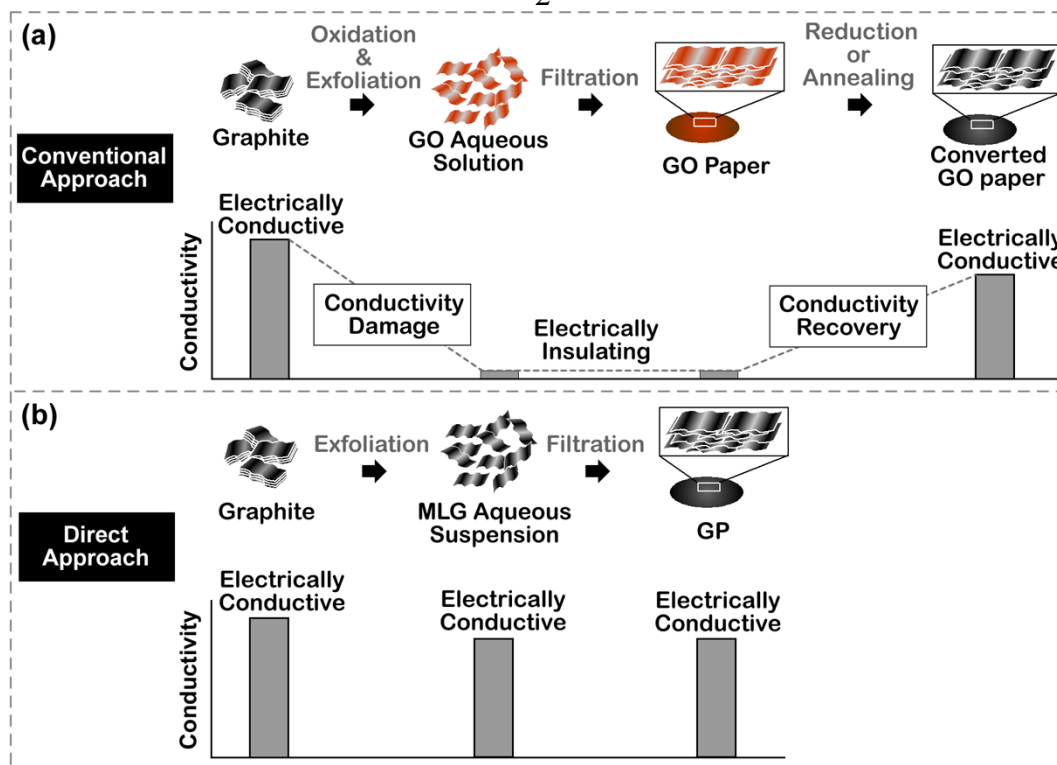


Figure S1 schematics of conventional approach for achieving chemical converted or thermal annealed graphene-oxide papers (a) and direct approach for achieving GPs in this work (b).

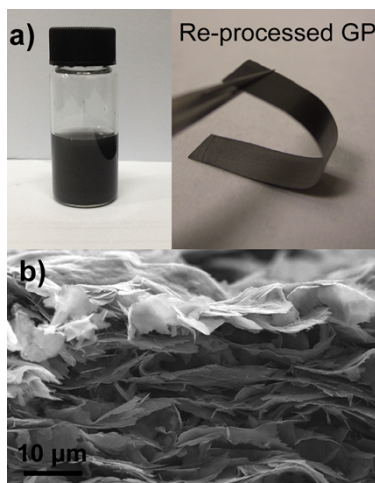


Figure S2 Re-dispersed aqueous MLG suspension and resulting re-processed GPs (a); SEM image of the re-processed GPs (b).

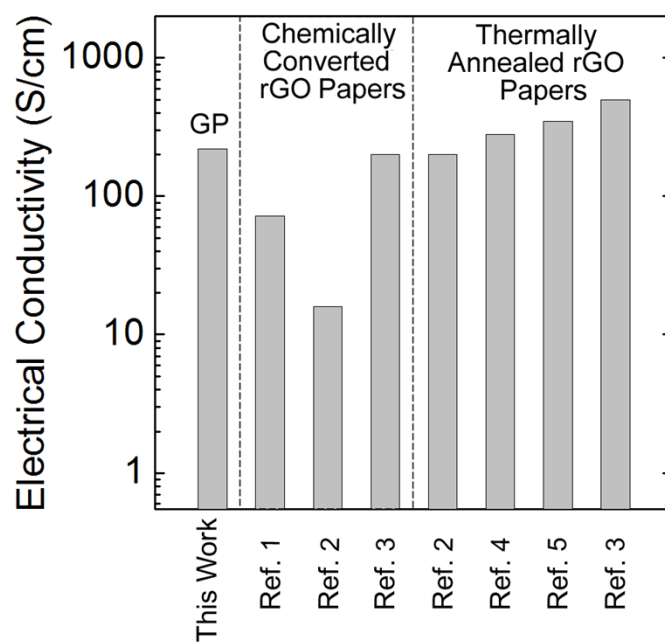


Figure S3 Electrical conductivity of the typical graphene oxide-based papers achieved by chemical conversion and thermal annealing.

Table S1 XPS analysis of C%, N%, O%, C/O ratio and C/N ratio in the GP and graphite sample.

The presence of N element should be associated with nitric acid used in the exfoliation process.

Sample	C (at.%)	N (at.%)	O (at.%)	C/O	C/N
GP	90.36	0.93	8.71	10.37	97.16
Graphite	96.95	-	3.05	31.79	-

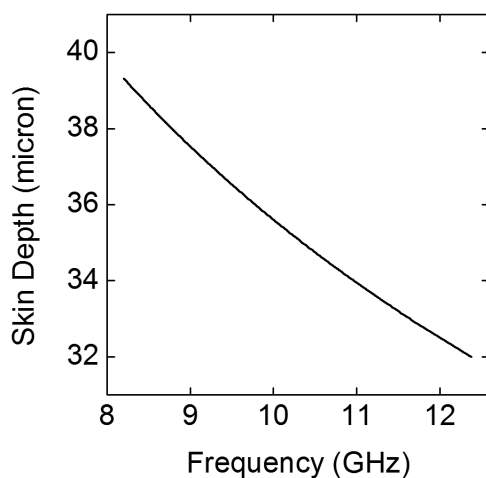


Figure S4 Estimated skin depth versus frequency for the GPs with average electrical conductivity ~ 200 S/cm.

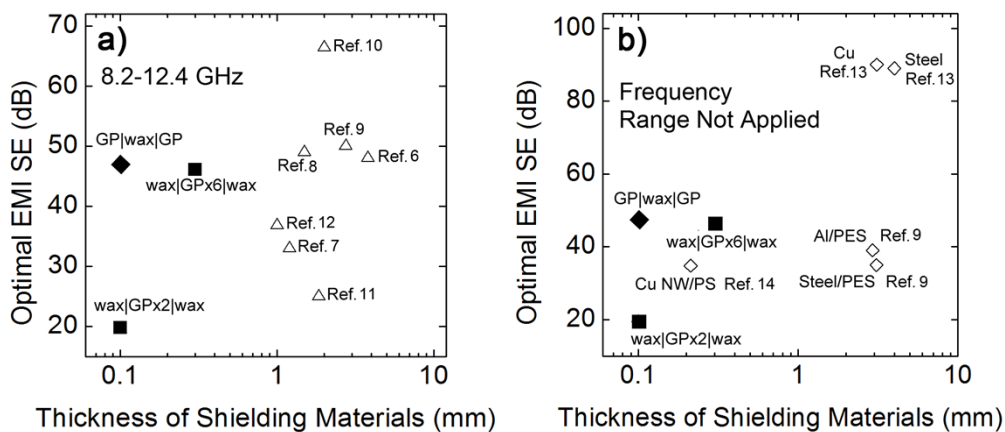


Figure S5 Optimal EMI SE performance with shielding thickness in carbon nanotube- and carbon fiber-based shielding materials (a) and other metal-based shielding materials (b).

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